

FFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jiong-Ping Lu
Serial No: 10/790,606
Examiner: Cuong Quang Nguyen
Filed: 03/01/2004
For: SEMICONDUCTOR DEVICE HAVING A SILICIDED GATE ELECTRODE AND METHOD OF MANUFACTURE THEREFOR

Docket No: TI-37479
Conf. No: 9593
Art Unit: 2811

ELECTION

Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

MAILING CERTIFICATE UNDER 37 C.F.R. § 1.8(a)

I hereby certify that the above correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on 4-12-05.


Ann Trent

Dear Sir:

This election is offered in response to the Examiner's restriction requirement mailed March 25, 2005.

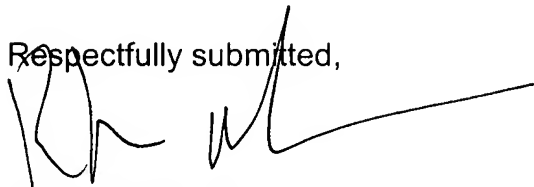
Applicant hereby elects to pursue claims 10-16, 18, and 19 directed to a method of silicided gate including a first metal layer and a second metal layer.

With regards to the election, Applicants state the following:

Claim 10 is generic as it is directed to silicided gate electrode including a first metal and a second metal. Such a limitation clearly includes two metal layers or an alloy of first and second metals. In addition, claim 11 includes the elected species of a first metal layer and a second metal layer and therefore must be included in the elected claims. Claim 17

is clearly directed to only an alloy and therefore was excluded from the elected set of claims.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'Peter K. McLarty', with a long horizontal flourish extending to the right.

Peter K. McLarty
Attorney for Applicant
Reg. No. 44,923

Texas Instruments Incorporated
P.O. Box 655474, MS 3999
Dallas, TX 75265
(972) 917-4258